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00.	State for form 14400 10			Application Number	10/576,345	
INFORMATION DISCLOSURE				Filing Date	April 18, 2006	
	TATEMENT I			First Named Inventor	MARCHAND, Gilles	
	I A I E III E III I	<i>.</i>	2.07	Art Unit	TBA	
	(use as many sheets as necessary)			Examiner Name	TBA	
Sheet	1	of	1	Attorney Docket Number	10404.039.00-US	

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Examiner Initials	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²		
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